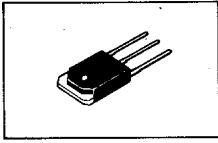


No.1397



# 2SC3482

NPN Triple Diffused Planar Type Silicon Transistor  
 FOR HIGH DEFINITION CRT DISPLAY HORIZONTAL  
 DEFLECTION OUTPUT APPLICATIONS  
 (BUILT-IN DAMPER DIODE)

**Features:**

- High breakdown voltage and high reliability
- High switching speed:  $t_f=0.3\mu s$  max.
- Capable of being mounted easily due to one-point fixing type plastic mold package

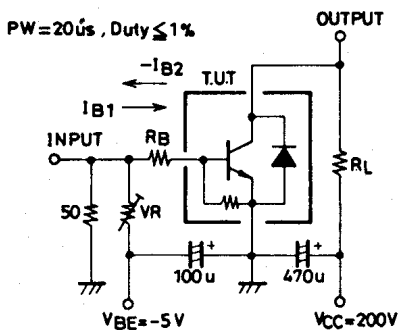
**Absolute Maximum Ratings at  $T_a=25^\circ C$**

			unit
Collector to Base Voltage	VCBO	1500	V
Collector to Emitter Voltage	VCEO	800	V
Emitter to Base Voltage	VEBO	7	V
Collector Current	IC	6	A
Peak Collector Current	icp	16	A
Collector Dissipation	PC	Tc=25°C	120 W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55 to +150	°C

**Electrical Characteristics at  $T_a=25^\circ C$**

			min	typ	max	unit
Collector Cutoff Current	ICBO	ICB=800V, IE=0			10	uA
Emitter Cutoff Current	IEBO	VEB=4V, IC=0	40		130	mA
DC Current Gain	hFE	VCE=5V, IC=1A	8			
Gain Bandwidth Product	fT	VCE=10V, IC=1A		3		MHz
C-E Saturation Voltage	VCE(sat)	IC=5A, IB=1.2A			5	V
B-E Saturation Voltage	VBE(sat)	IC=5A, IB=1.2A			1.5	V
C-B Breakdown Voltage	V(BR)CBO	IC=5mA, IE=0	1500			V
C-E Breakdown Voltage	V(BR)CEO	IC=5mA, RBE=∞	800			V
E-B Breakdown Voltage	V(BR)EBO	IE=200mA, IC=0	7			V
Diode Forward Voltage	VF	IEC=6A			2	V
Storage Time	tstg	[ IC=5A, IB1=1A, IB2=-2A, VCC=200V, RL=40ohm ]			3.0	us
Fall Time	tf				0.3	us

**Switching Time Test Circuit**



**Case Outline 2022  
(unit:mm)**

